

SMPS MOSFET **IRF6218SPbF**
IRF6218LPbF
HEXFET® Power MOSFET

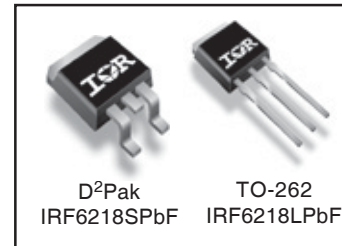
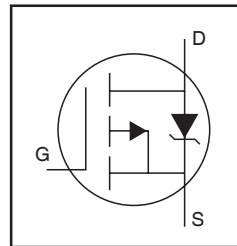
Applications

- Reset Switch for Active Clamp
Reset DC-DC converters

V_{DSS}	$R_{DS(on)}$ max	I_D
-150V	150mΩ @ $V_{GS} = -10V$	-27A

Benefits

- Low Gate to Drain Charge to Reduce
Switching Losses
- Fully Characterized Capacitance Including
Effective C_{OSS} to Simplify Design (See
App. Note AN1001)
- Fully Characterized Avalanche Voltage
and Current
- Lead-Free



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	-150	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ $T_C = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	-27	A
I_D @ $T_C = 100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	-19	
I_{DM}	Pulsed Drain Current ①	-110	
P_D @ $T_C = 25^\circ C$	Maximum Power Dissipation	250	W
	Linear Derating Factor	1.6	W/°C
dv/dt	Peak Diode Recovery dv/dt ②	8.2	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑤	—	0.61	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady state)⑤⑥	—	40	

Notes ① through ⑥ are on page 9

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-150	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.17	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = -1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	120	150	m Ω	$V_{GS} = -10V, I_D = -16A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-3.0	—	-5.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-25	μA	$V_{DS} = -120V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -120V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

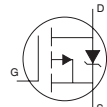
	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	11	—	—	S	$V_{DS} = -50V, I_D = -16A$
Q_g	Total Gate Charge	—	71	110	nC	$I_D = -16A$
Q_{gs}	Gate-to-Source Charge	—	21	—		$V_{DS} = -120V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	32	—		$V_{GS} = -10V$ ④
$t_{d(on)}$	Turn-On Delay Time	—	21	—	ns	$V_{DD} = -75V$
t_r	Rise Time	—	70	—		$I_D = -16A$
$t_{d(off)}$	Turn-Off Delay Time	—	35	—		$R_G = 3.9\Omega$
t_f	Fall Time	—	30	—		$V_{GS} = -10V$ ④
C_{iss}	Input Capacitance	—	2210	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	370	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	89	—		$f = 1.0MHz$
C_{oss}	Output Capacitance	—	2220	—		$V_{GS} = 0V, V_{DS} = -1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	170	—		$V_{GS} = 0V, V_{DS} = -120V, f = 1.0MHz$
$C_{oss\ eff.}$	Effective Output Capacitance	—	340	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } -120V$

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	210	mJ
I_{AR}	Avalanche Current ①	—	-16	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-27	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-110		
V_{SD}	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}, I_S = -16A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	150	—	ns	$T_J = 25^\circ\text{C}, I_F = -16A, V_{DD} = -25V$
Q_{rr}	Reverse Recovery Charge	—	860	—	nC	$di/dt = -100A/\mu s$ ④



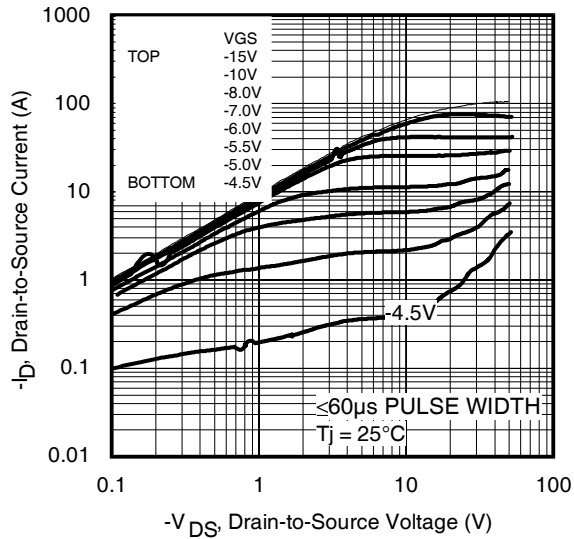


Fig 1. Typical Output Characteristics

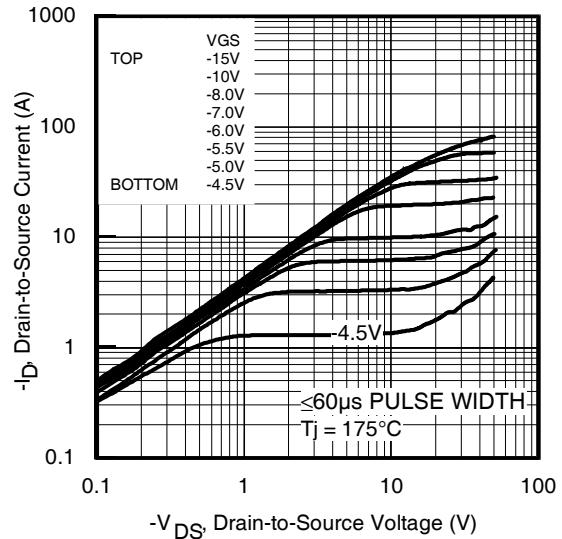


Fig 2. Typical Output Characteristics

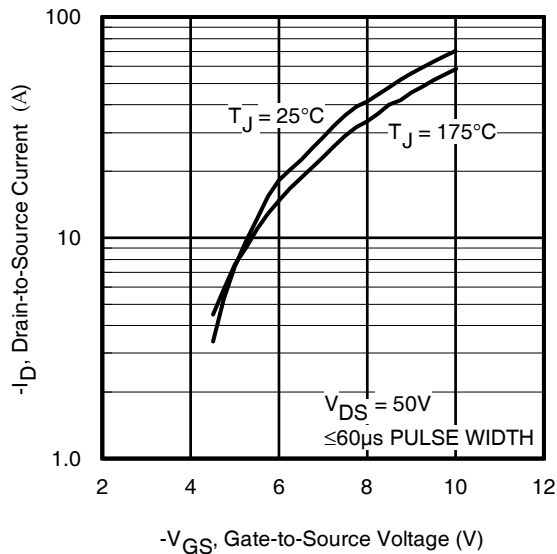


Fig 3. Typical Transfer Characteristics

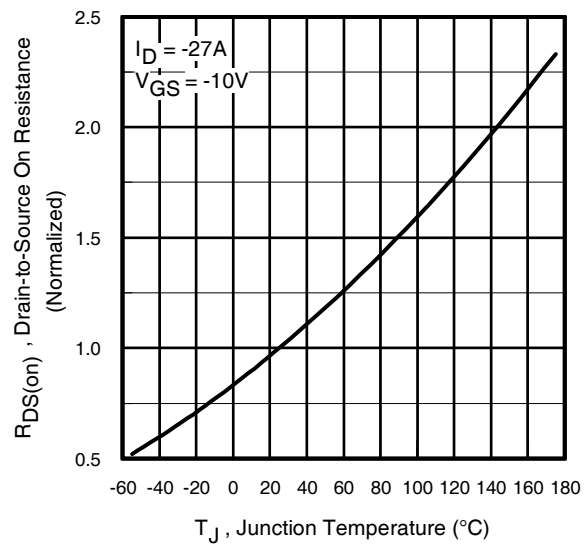


Fig 4. Normalized On-Resistance vs. Temperature

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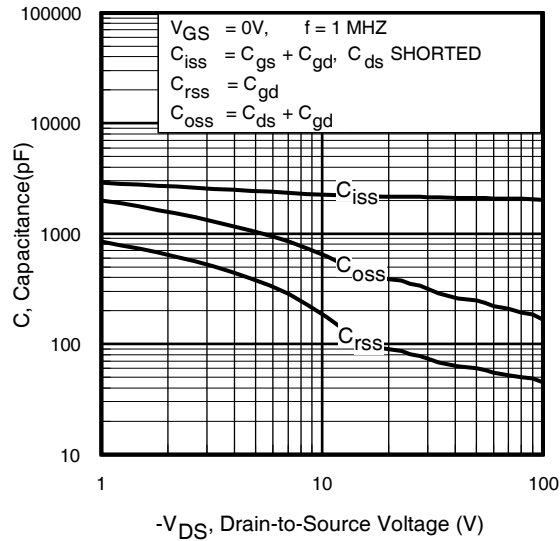


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

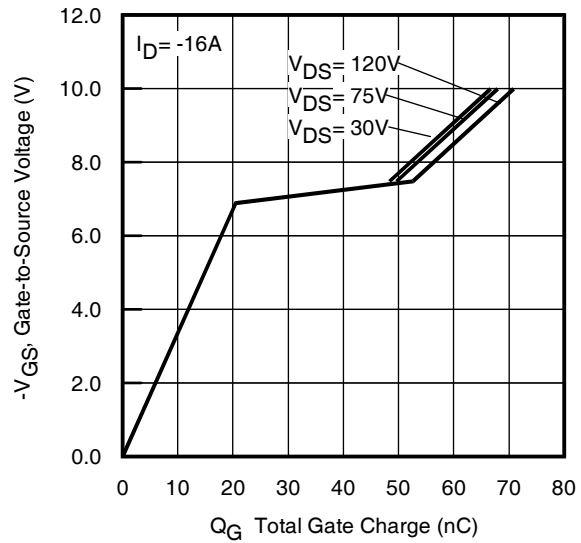


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

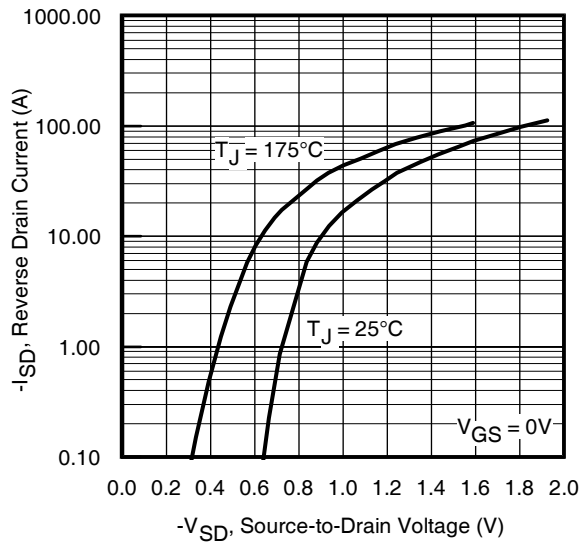


Fig 7. Typical Source-Drain Diode Forward Voltage

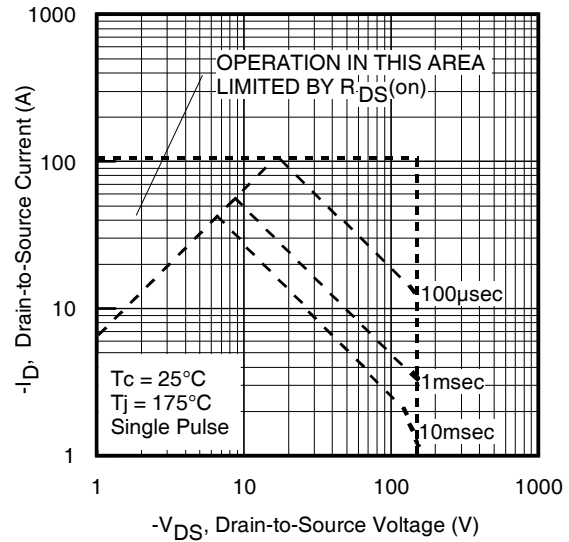


Fig 8. Maximum Safe Operating Area

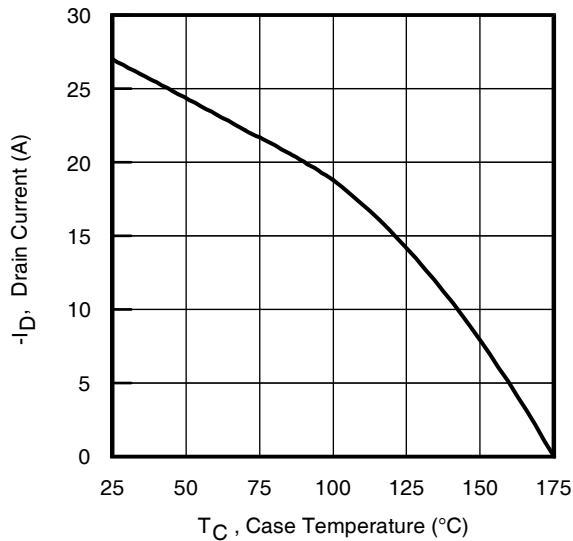


Fig 9. Maximum Drain Current vs. Ambient Temperature

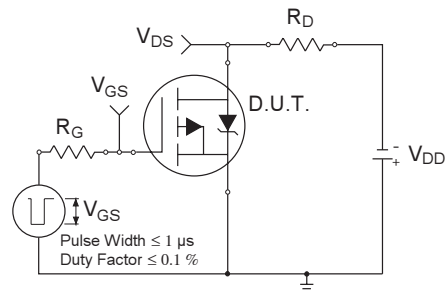


Fig 10a. Switching Time Test Circuit

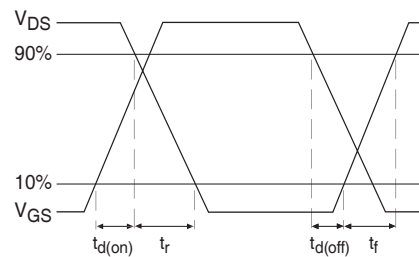


Fig 10b. Switching Time Waveforms

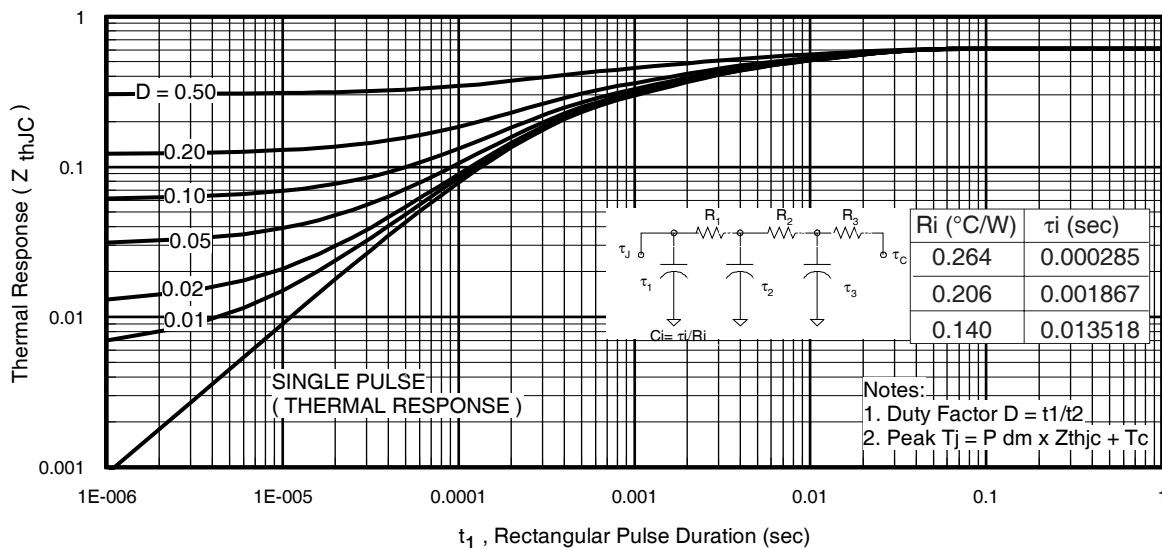
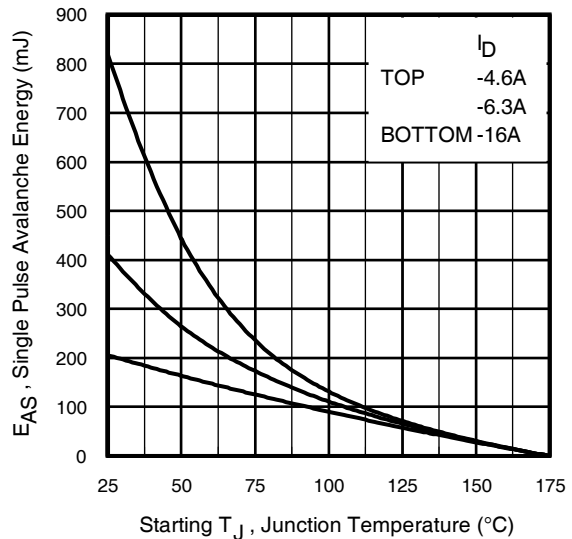
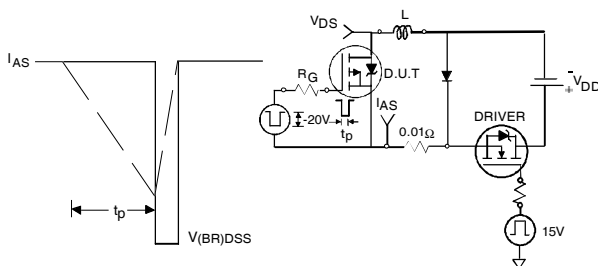
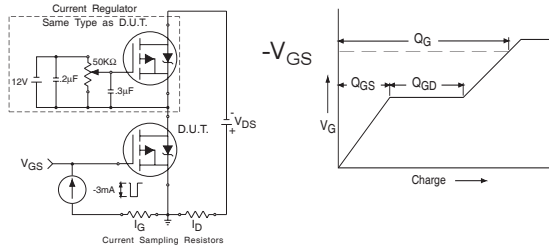
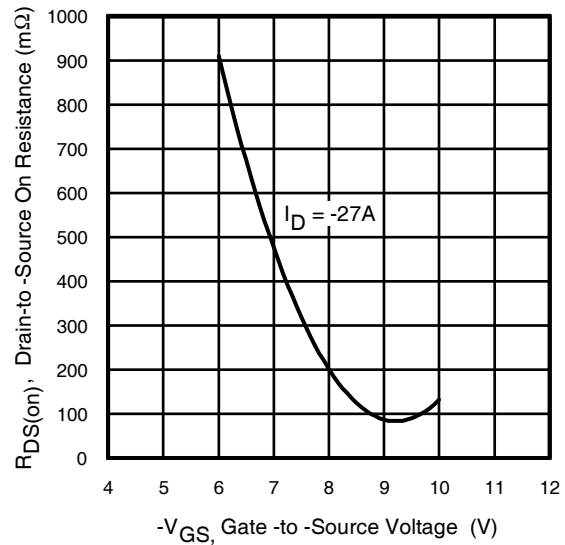
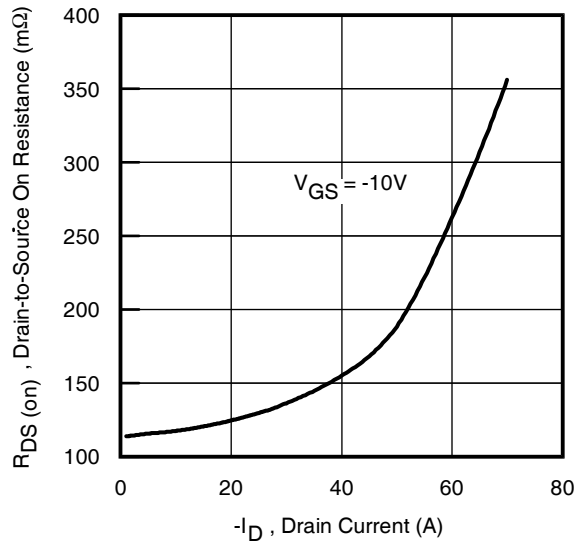


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

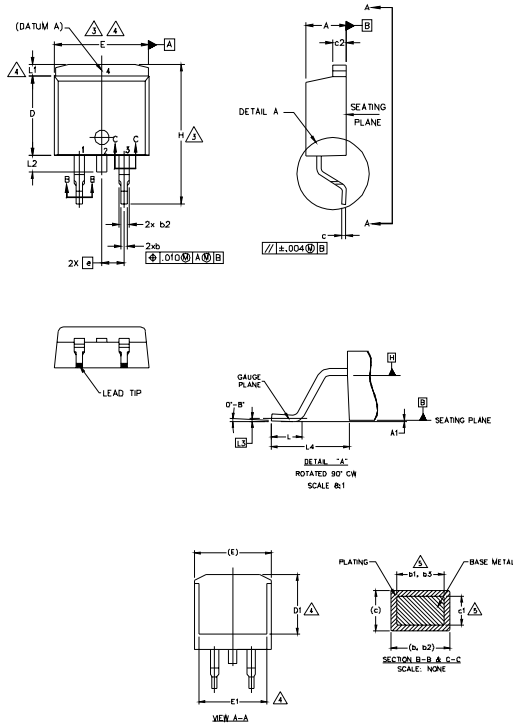
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D²Pak (TO-263AB) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
 4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
 5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 7. CONTROLLING DIMENSION: INCH.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	5
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.78	.045	.070	5
b3	1.14	1.73	.045	.068	
c	0.38	0.74	.015	.029	5
c1	0.38	0.58	.015	.023	
c2	1.14	1.65	.045	.065	3
D	8.38	9.65	.330	.380	
D1	6.86	—	.270	—	4
E	9.65	10.67	.380	.420	
E1	6.22	—	.245	—	4
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	4
L	1.78	2.79	.070	.110	
L1	—	1.65	—	.066	
L2	1.27	1.78	—	.070	
L3	0.25 BSC		.010 BSC		4
L4	4.78	5.28	.188	.208	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
2. 4.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

- 1.- GATE
2. 4.- COLLECTOR
- 3.- EMITTER

DIODES

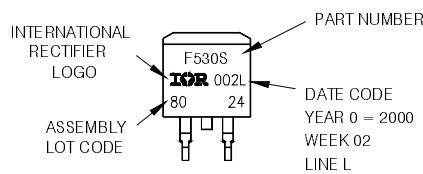
- 1.- ANODE *
2. 4.- CATHODE
- 3.- ANODE

* PART DEPENDENT.

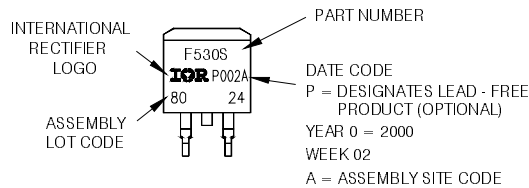
D²Pak (TO-263AB) Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE 'L'

Note: "P" in assembly line position
indicates "Lead - Free"



OR



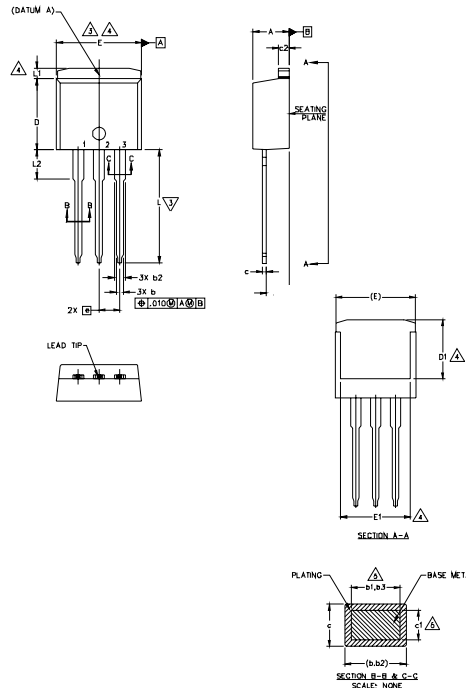
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>
www.irf.com

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TO-262 Package Outline

Dimensions are shown in millimeters (inches)

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION: INCH.
7. OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.) AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	3.02	.080	.119	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	—	.270	—	4
E	9.65	10.67	.380	.420	3, 4
E1	6.22	—	.245	—	4
e	2.54 BSC		.100 BSC		
L	13.46	14.10	.530	.555	
L1	—	1.65	—	.065	4
L2	3.56	3.71	.140	.146	

LEAD ASSIGNMENTS

HEXFET

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

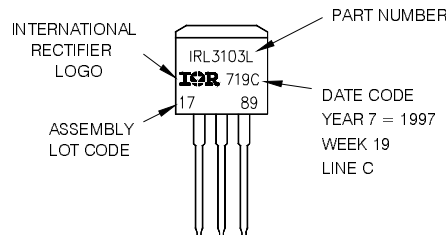
IGBTs, CoPACK

1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

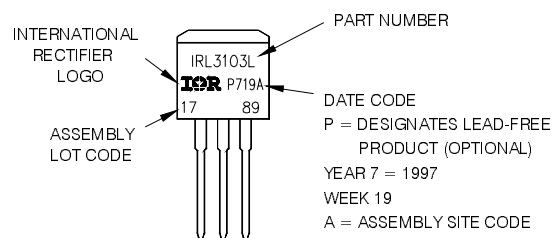
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE 'C'

Note: "P" in assembly line position
indicates "Lead - Free"



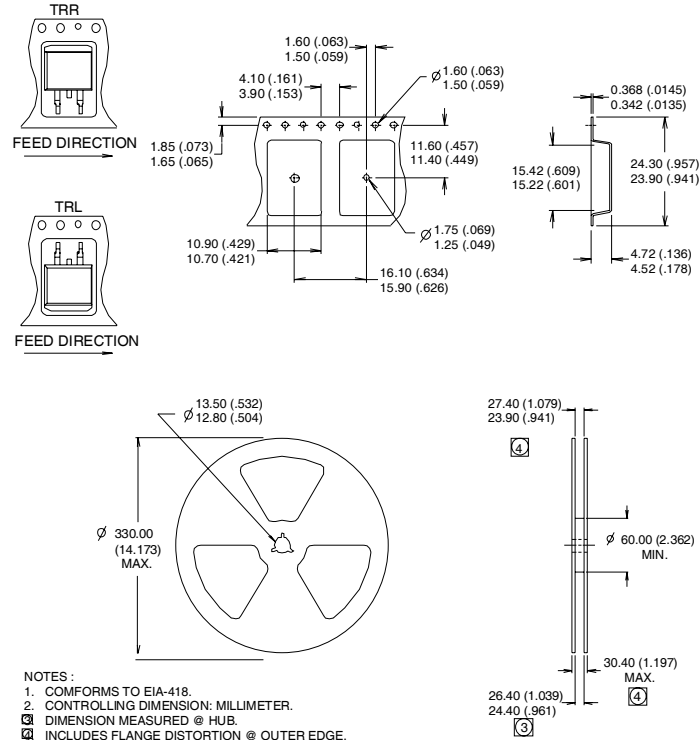
OR



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.6\text{mH}$, $R_G = 25\Omega$, $I_{AS} = -17\text{A}$.
- ③ $I_{SD} \leq -17\text{A}$, $di/dt \leq -520\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ R_{θ} is measured at T_J of approximately 90°C .
- ⑥ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.

This product has been designed and qualified for the Industrial market.

Qualification Standards can be found on IR's Web site.